

Far-Field EMI Analysis Methodology and Verification on SSD Boards

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SPEAKERS



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Agenda

- **Background**
 - Trends of Data Storage
 - Necessity of EMI Simulation Methodology
- **Far-Field EMI Simulation Methodology**
 - Proposed EMI Simulation Flow
 - PCB-Level EMI Solution
- **Correlation with Far-Field Measurement Results**
- **Relationship Between Board Design and Far-Field EMI**
- **Conclusion**



Trends of Data Storage

- Hard Disk Drive (HDD) → Solid-State Drive (SSD)
 - *Higher* Read/Write Rate, *Faster* Access Time, *Lower* Power Consumption



Source: www.google.com

SSD



Source: www.samsung.com

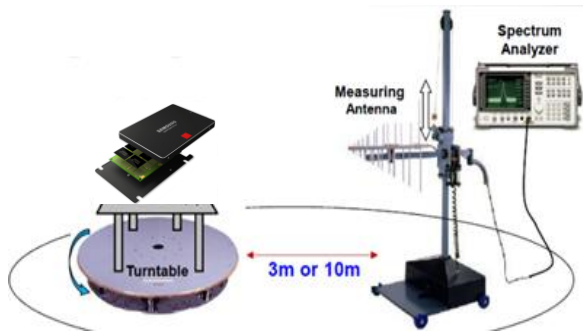
		SSD	HDD	Difference
Media		NAND FLASH	Magnetic Platters	
Read/Write Speed	Sequential [MB/s]	540 / 330	60 / 160	x 9 / 2
	Random [IOPS*]	98000 / 70000	450/400	x 217 / 175
Data Access Time [ms]		0.1	10~12	x 100~120
Power Consumption	Active/Idle [W]	0.127(0.046)	1.75(0.8)	x 13 ↓ (x 17 ↓)



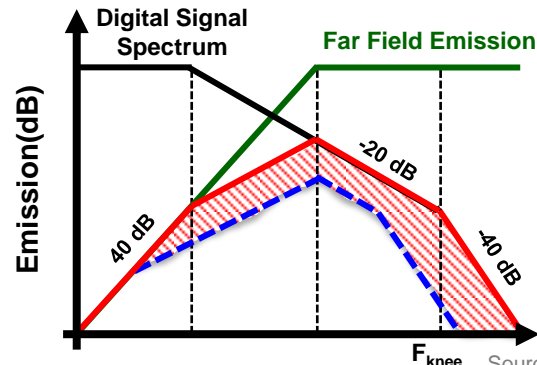
EMI Problem in SSD Products

- SSD's speed and density is continuously increasing

Far-Field EMI Measurement Setup

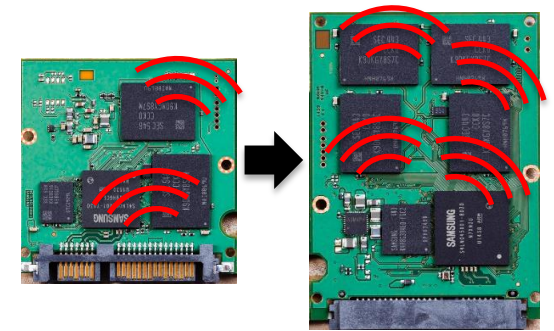


Increasing Speed



- Overall Emission Spectrum (Speed x1)
- Overall Emission Spectrum (Speed x2)

Increasing Density

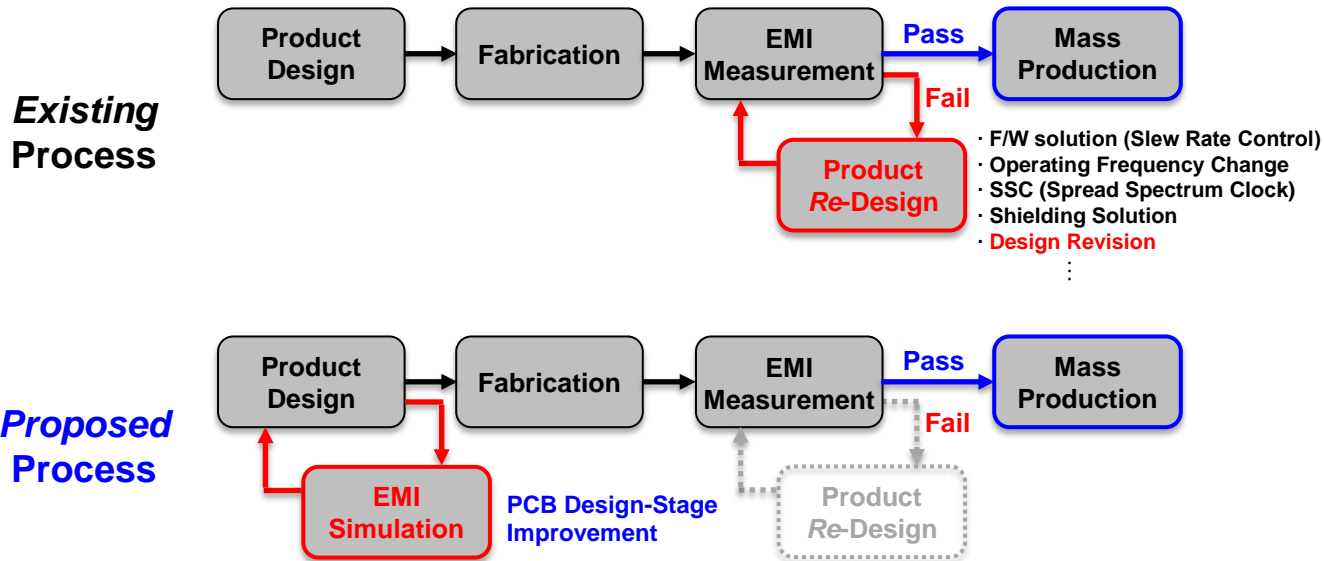


Source: www.google.com

EMI (Electromagnetic Interference) becomes a critical issue!

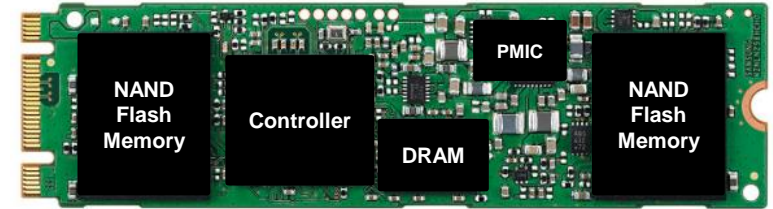
Necessity of EMI Simulation Methodology

- Measurement-based EMI verification requires **additional cost and time** to debug
- EMI mechanisms and root causes of the radiated field need to analyze

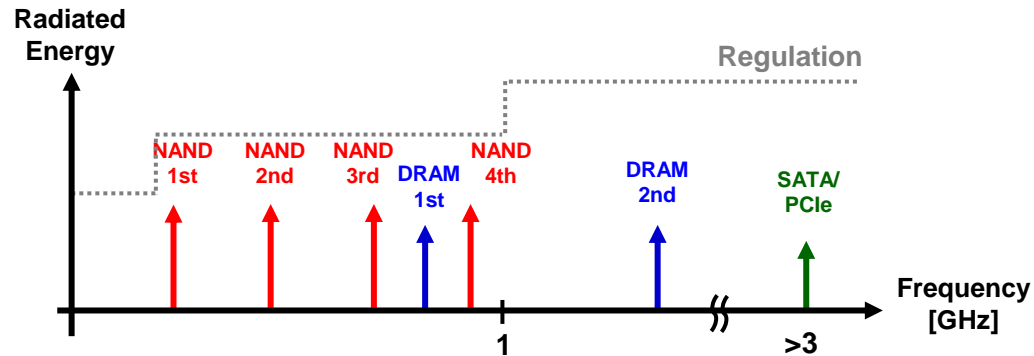


EMI Noises in SSD Products

- Composed of various devices
 - NAND, DRAM, CTRL, PMIC ...
 - Operated with different speeds / voltages
- Data Path
 - **NAND interface**, DRAM interface, Host interface
 - ➔ Higher supply voltage, longer board routing

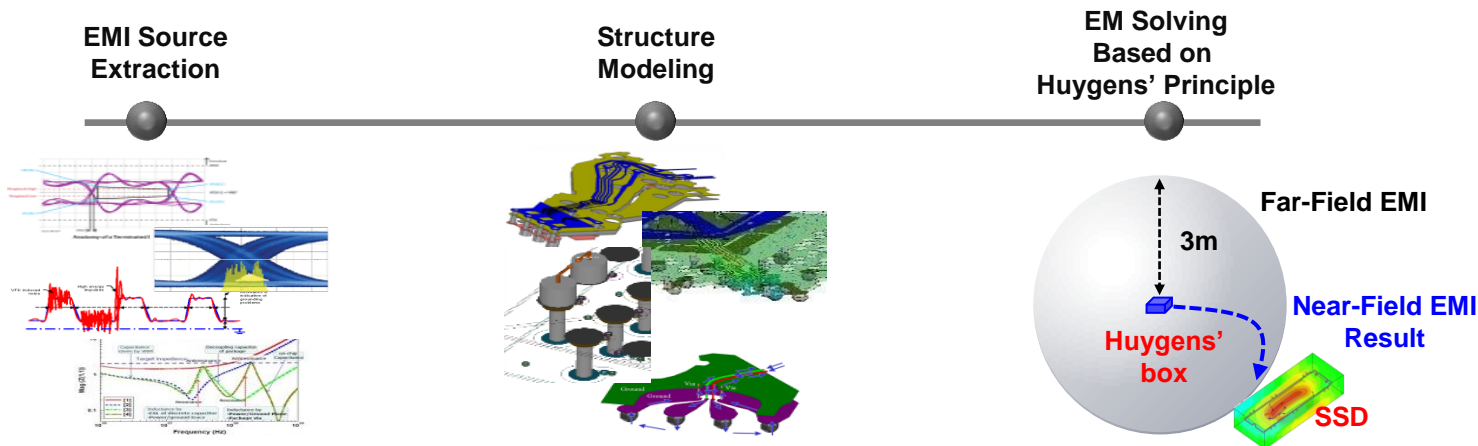


Source: www.samsung.com



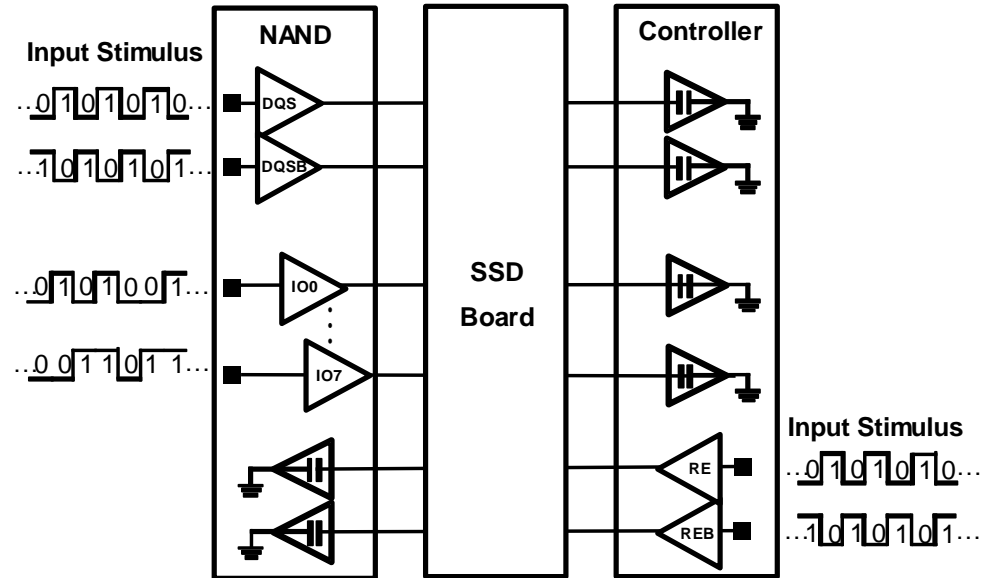
Proposed Far-Field EMI Simulation Flow

- Far-field EMI simulation methodology [Ref. APEMC2015, Benson Wei *et. al.*]
- Propose 3 items to enhance simulation *accuracy* and *efficiency*
 - EMI source extraction
 - Package and reference plane modeling
 - Huygens' box optimization for N/F to F/F transform



Stage 1: EMI Source Extraction

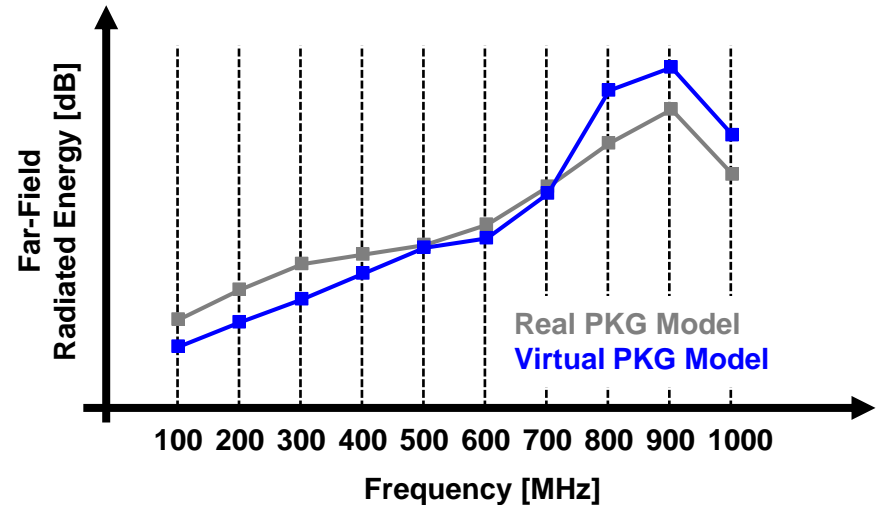
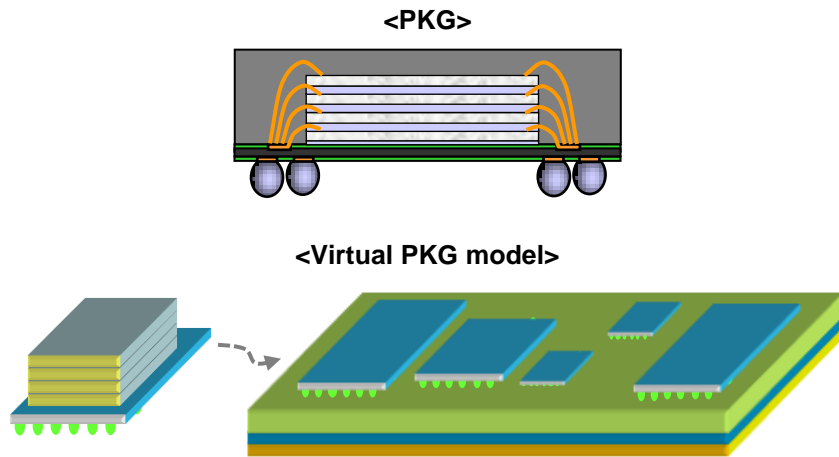
- Read operation at 460 Mbps
(NAND to Controller Interface)
- Block diagram
 - NAND Flash I/O buffer
 - Controller I/O buffer
 - Board model (S-parameter)
- Input Stimulus
 - I/O Buffer : PRBS 2^7-1
 - Strobe and clock signals
 - Periodic pattern
 - 5% duty cycle distortion
 - : To include power noise



Stage 2: Structure Modeling (1)

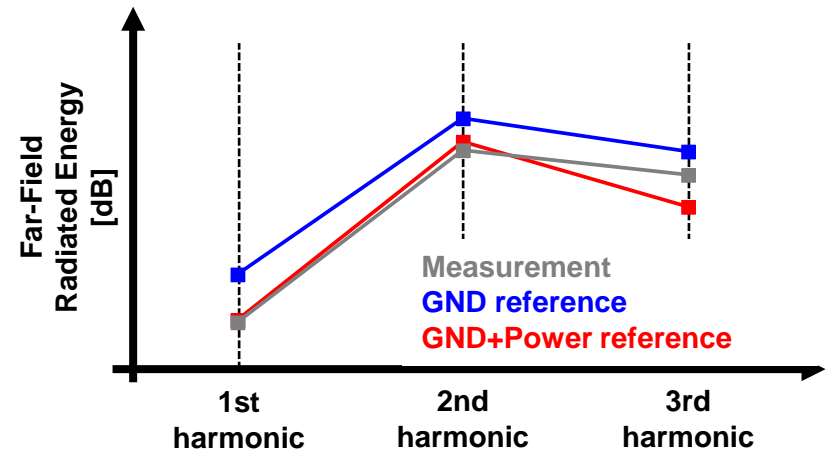
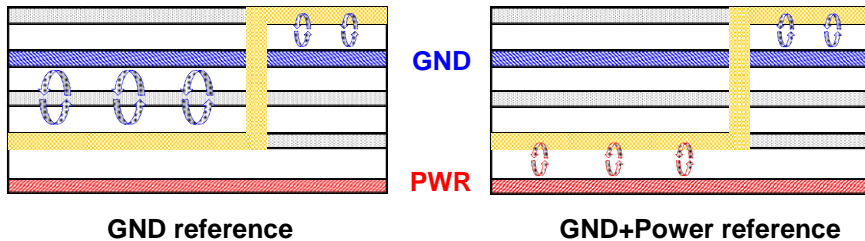
- EM simulation with package and board together
 - Impractical solution due to *simulation time* and *hardware resources*
- Propose virtual package model with metal plane

→ Both results shows similar simulation results



Stage 2: Structure Modeling (2)

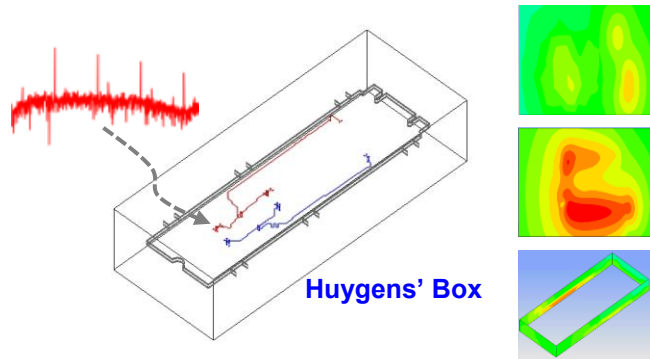
- Propose the merged reference plane
 - Power and ground plane are modeled in connection to the one plane
 - ➔ Represents return path through the capacitor of the die
 - Simulation result is similar to the measurement



Stage 3: EM Solving Based on Huygens' Principle

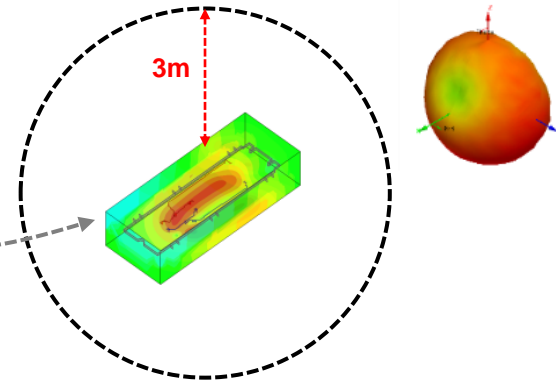
- Proposed near- to far-field transform method based on Huygens' principle
 - Radiated energy simulation at 3-m distance from micro-unit SSD board

N/F Simulation – 2.5D EM solver



Attach I/O current as EMI source

F/F Simulation – 3D EM solver



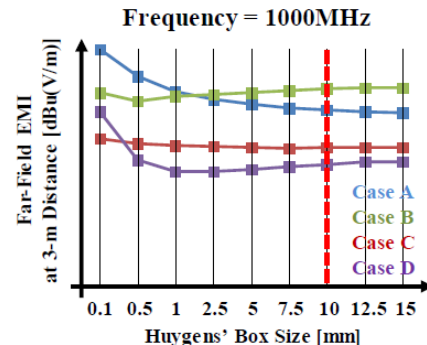
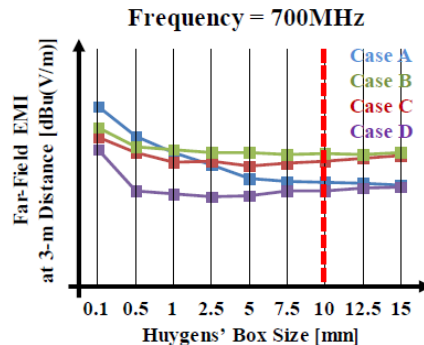
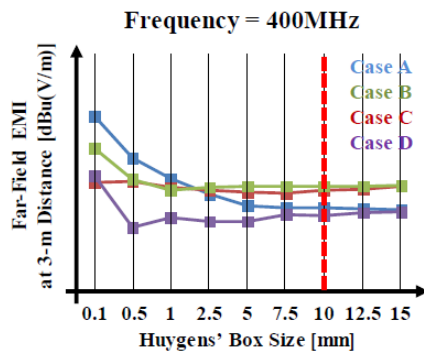
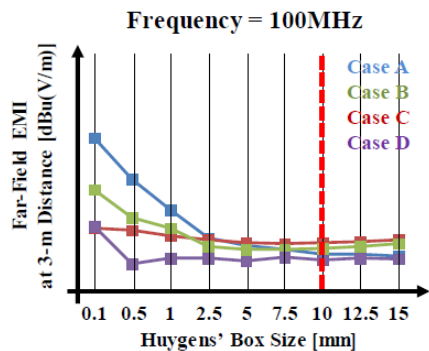
Maximum electric field calculation at 3-m sphere surface

How to optimize Huygens' box size?

Stage 3: EM Solving Based on Huygens' Principle

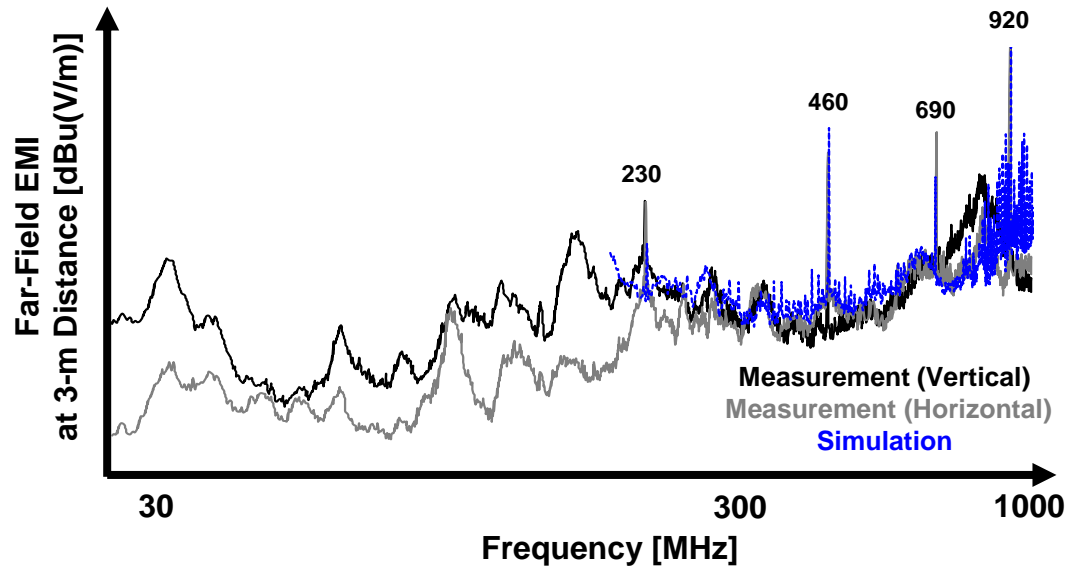
▪ Huygens' box size optimization

- Proper box size is necessary to minimize error for near- to-far field transform
- The radiated field is saturated from **10mm** box size



Correlation with Far-Field Measurement Results

- NAND read operation (460Mbps)
- Good agreement up to 1GHz between simulation and measurement



Measurement (Vertical)

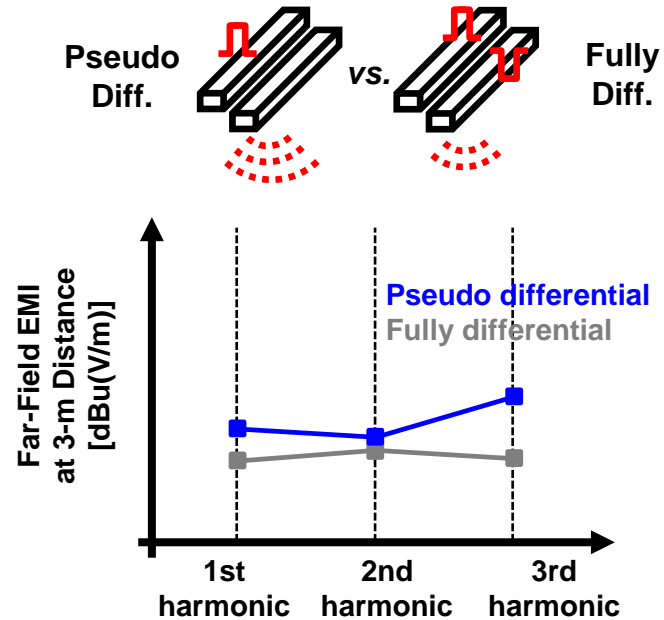
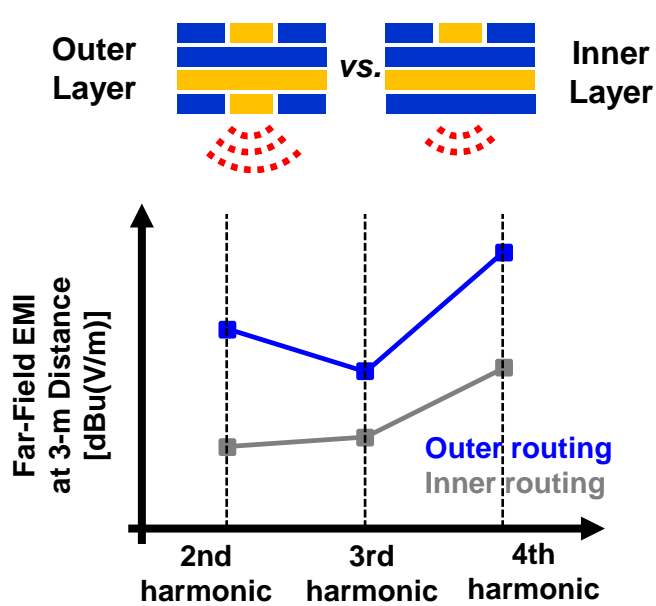


Measurement (Horizontal)



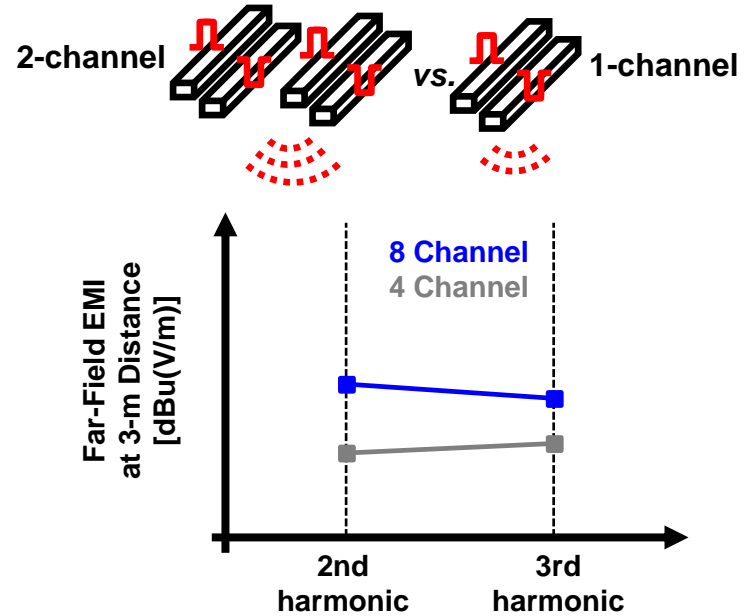
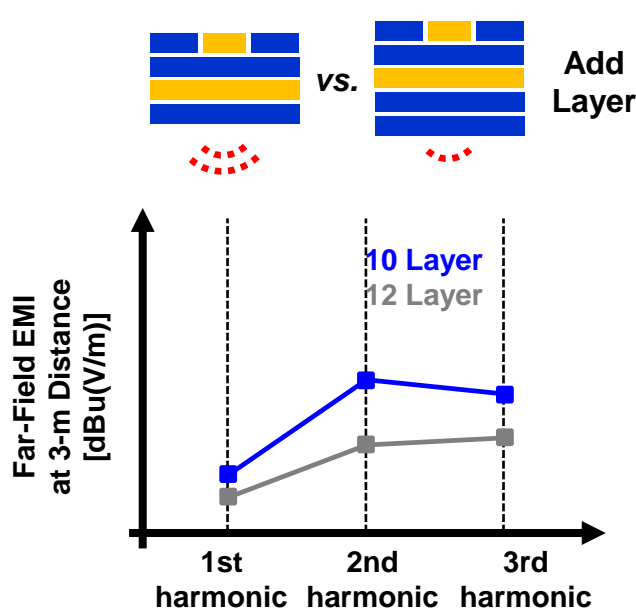
Case Analysis (1)

- Investigate on relationship between board design and far-field EMI
 - Routing scheme, Signaling scheme, Number of layer, Number of channel



Case Analysis (2)

- Investigate on relationship between board design and far-field EMI
 - Routing scheme, Signaling scheme, **Number of layer**, **Number of channel**



Conclusion

- **Far-field EMI analysis methodology for commercial SSD products**
 - EMI source extraction
 - PCB structure modeling
 - EM solving method based on Huygens' principle

- **Good correlation between simulation and measurement**

- **Investigation of the relationship between board designs and the radiated energy**
 - Routing scheme, signaling scheme, number of layer and number of channel

- **EMI analysis in the design stage prior to the manufacturing process**



Thank you!

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QUESTIONS?

